



ABSTRACT OF THE DISCLOSURE

Disclosed is a detector with quantum structure comprising a small-gap semiconductor material inserted between two large-gap semiconductor materials, the
5 structure comprising a coupling grating between the wave to be detected and the detector zone constituted by the small-gap material. Under these conditions, the detector zone may have a very small thickness (typically of the order of 1,000 Å) and lead to a
10 detectivity, limited by the dark current, that is high.
Figure 3

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